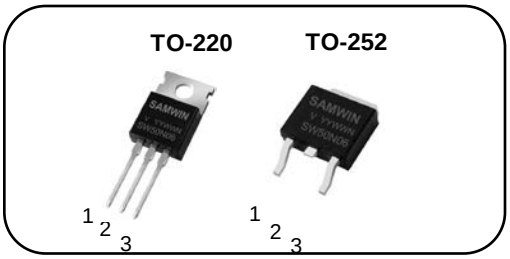
N-channel Enhancement mode TO-220/TO-252 MOSFET

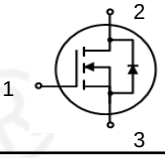
Features

- High ruggedness
- $R_{DS(ON)}$ (Typ 10mΩ)@V_{GS}=10V
- Gate Charge (Typ 43nC)
- Improved dv/dt Capability
- 100% Avalanche Tested
- Application: DC-DC, Motor control



1. Gate 2. Drain 3. Source

BV_{DSS} : 60V
I_D : 50A
$R_{DS(ON)}$: 10mΩ



General Description

This power MOSFET is produced with advanced technology of SAMWIN.
This technology enable power MOSFET to have better characteristics, such as fast switching time, low on resistance, low gate charge and especially excellent avalanche characteristics.

Order Codes

Item	Sales Type	Marking	Package	Packaging
1	SW P 50N06V	SW50N06V	TO-220	TUBE
2	SW D 50N06V	SW50N06V	TO-252	TUBE

Absolute maximum ratings

Symbol	Parameter		Value		Unit
			TO-220	TO-252	
V_{DSS}	Drain to Source Voltage		60		V
I_D	Continuous Drain Current (@T_C=25°C)		50*		A
	Continuous Drain Current (@T_C=100°C)		31.5*		A
I_{DM}	Drain current pulsed	(note 1)	200		A
V_{GS}	Gate to Source Voltage		±20		V
E_{AS}	Single pulsed Avalanche Energy	(note 2)	200		mJ
E_{AR}	Repetitive Avalanche Energy	(note 1)	28		mJ
dv/dt	Peak diode Recovery dv/dt	(note 3)	5		V/ns
P_D	Total power dissipation (@T_C=25°C)		74	57	W
	Derating Factor above 25°C		0.6	0.5	W/°C
T_{STG}, T_J	Operating Junction Temperature & Storage Temperature		-55 ~ + 150		°C
T_L	Maximum Lead Temperature for soldering purpose, 1/8 from Case for 5 seconds.		300		°C

*. Drain current is limited by junction temperature.

Thermal characteristics

Symbol	Parameter	Value		Unit
		TO-220	TO-252	
R_{thjc}	Thermal resistance, Junction to case	1.7	2.2	°C/W
R_{thcs}	Thermal resistance, Case to Sink	0.5		°C/W
R_{thja}	Thermal resistance, Junction to ambient	50	70.4	°C/W

Electrical characteristic (T_C = 25ºC unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
Off characteristics						
BV_{DSS}	Drain to source breakdown voltage	V_{GS}=0V, I_D=250uA	60			V
ΔBV_{DSS} / ΔT_J	Breakdown voltage temperature coefficient	I_D=250uA, referenced to 25ºC		0.04		V/ºC
I_{DSS}	Drain to source leakage current	V_{DS}=60V, V_{GS}=0V			1	uA
		V_{DS}=48V, T_C=125ºC			50	uA
I_{GSS}	Gate to source leakage current, forward	V_{GS}=20V, V_{DS}=0V			100	nA
	Gate to source leakage current, reverse	V_{GS}=-20V, V_{DS}=0V			-100	nA
On characteristics						
$V_{GS(TH)}$	Gate threshold voltage	V_{DS}=V_{GS}, I_D=250uA	1.2		2.5	V
$R_{DS(ON)}$	Drain to source on state resistance	V_{GS}=10V, I_D = 25A		10	13	mΩ
Gfs	Forward Transconductance	V_{DS} = 10 V, I_D = 25A		149		S
Dynamic characteristics						
C_{iss}	Input capacitance	V_{GS}=0V, V_{DS}=25V, f=1MHz		2340		pF
C_{oss}	Output capacitance			154		
C_{rss}	Reverse transfer capacitance			120		
$t_{d(on)}$	Turn on delay time	V_{DS}=30V, I_D=50A, R_G=25Ω (note 4,5)		10		nS
tr	Rising time			47		
$t_{d(off)}$	Turn off delay time			131		
t_f	Fall time			112		
Q_g	Total gate charge	V_{DS}=50V, V_{GS}=10V, I_D=50A (note 4,5)		43		nC
Q_{gs}	Gate-source charge			3.5		
Q_{gd}	Gate-drain charge			16		

Source to drain diode ratings characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_S	Continuous source current	Integral reverse p-n Junction diode in the MOSFET			50	A
I_{SM}	Pulsed source current				200	A
V_{SD}	Diode forward voltage drop.	I_S=50A, V_{GS}=0V			1.4	V
T_{rr}	Reverse recovery time	I_S=50A, V_{GS}=0V, dI_F/dt=100A/us		13		nS
Q_{rr}	Reverse recovery Charge			5.24		nC

※. Notes

1. Repeatitive rating : pulse width limited by junction temperature.
2. L = 6.3mH, I_{AS} = 8A, V_{DD} = 50V, R_G=25Ω, Starting T_J = 25ºC
3. I_{SD} ≤50A, di/dt = 100A/us, V_{DD} ≤ BV_{DSS}, Staring T_J =25ºC
4. Pulse Test : Pulse Width ≤ 300us, duty cycle ≤ 2%.
5. Essentially independent of operating temperature.

Fig. 1. On-state characteristics

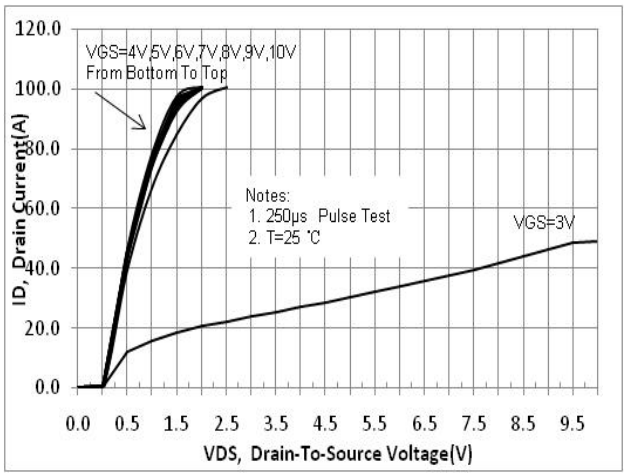


Fig. 2. On-resistance variation vs. drain current and gate voltage

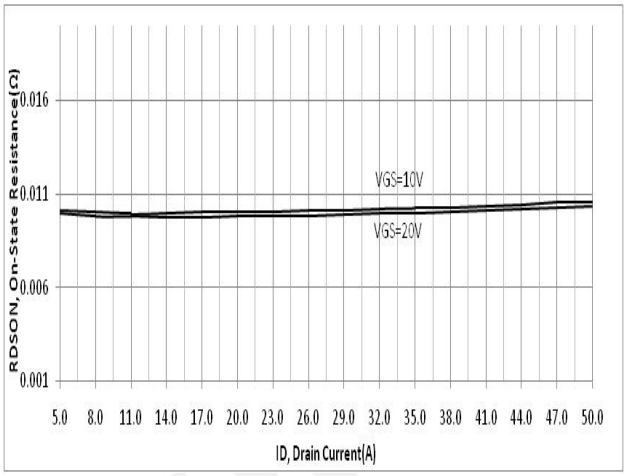


Fig. 3. Gate charge characteristics

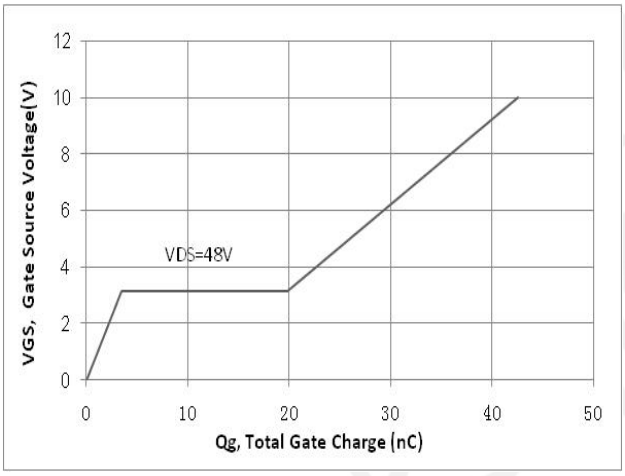


Fig. 4. On state current vs. diode forward voltage

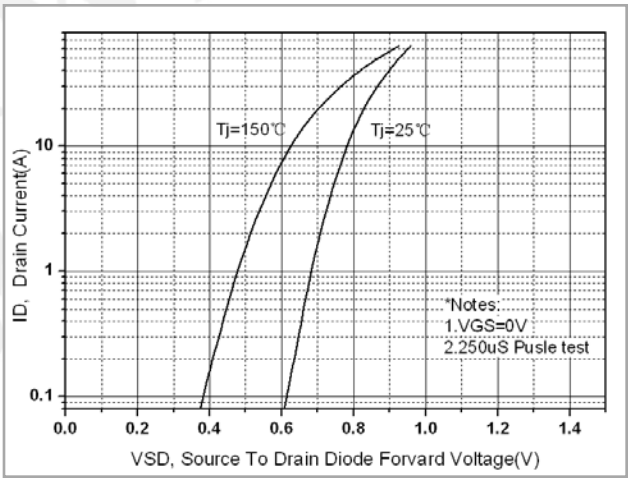


Fig 5. Breakdown Voltage Variation vs. Junction Temperature

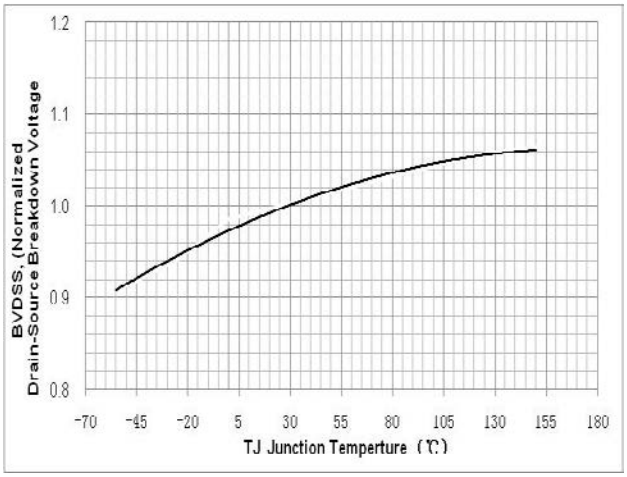


Fig. 6. On resistance variation vs. junction temperature

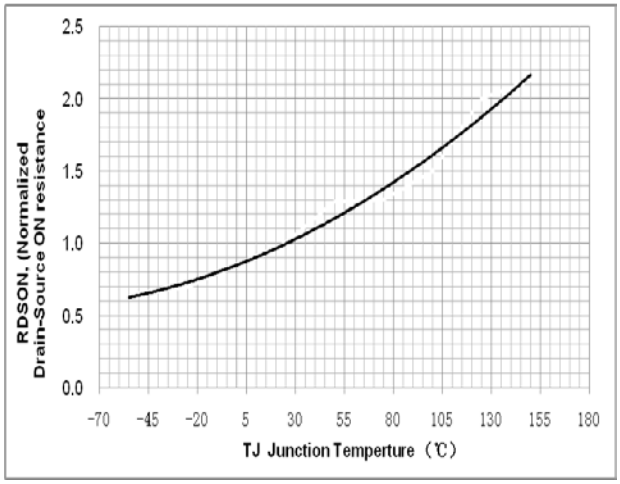


Fig. 7. Maximum safe operating area(TO-220)

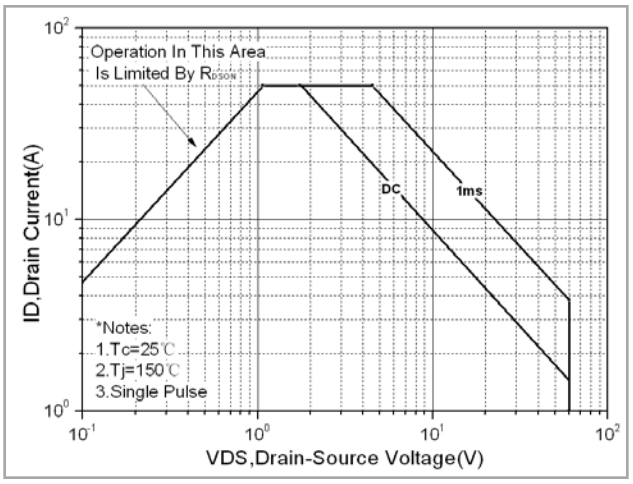


Fig. 8. Transient thermal response curve(TO-220)

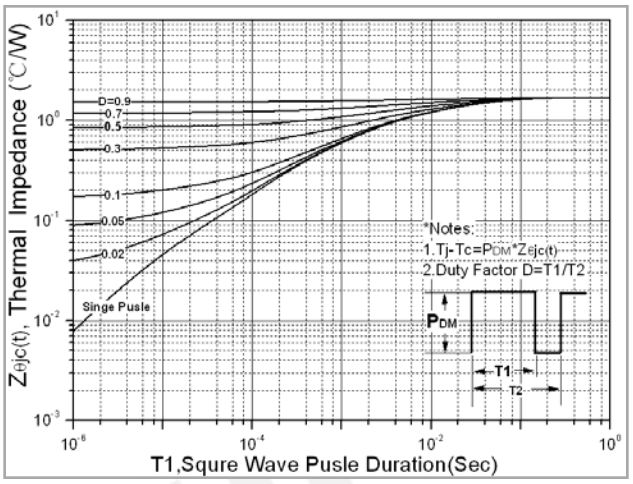


Fig. 9. Maximum safe operating area(TO-252)

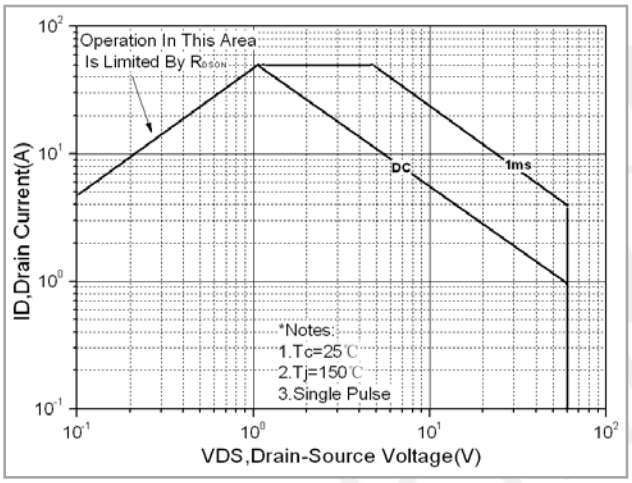


Fig. 10. Transient thermal response curve(TO-252)

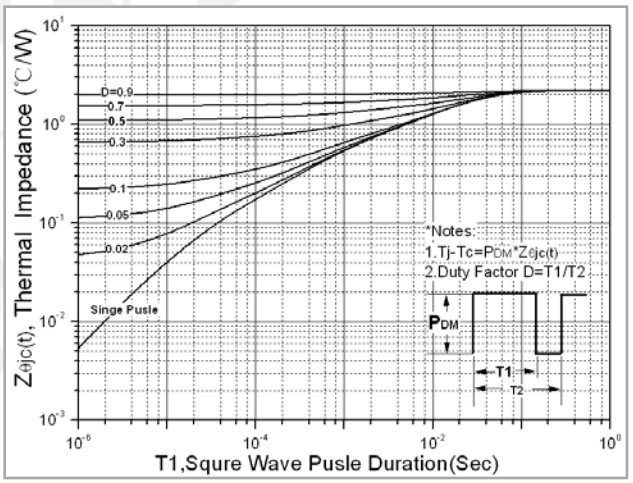


Fig. 11. Capacitance Characteristics

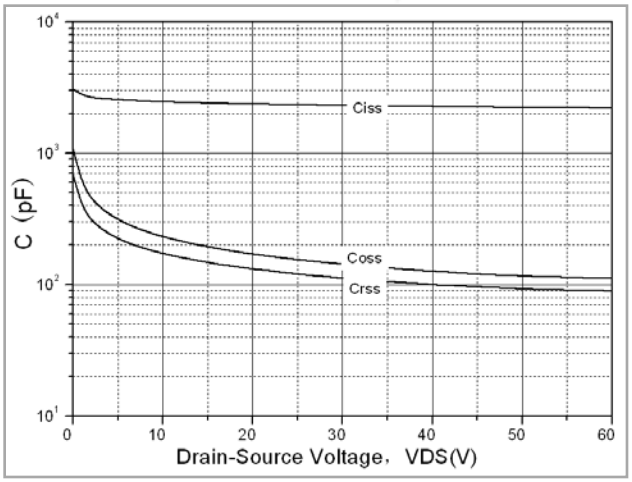


Fig. 12. Gate charge test circuit & waveform

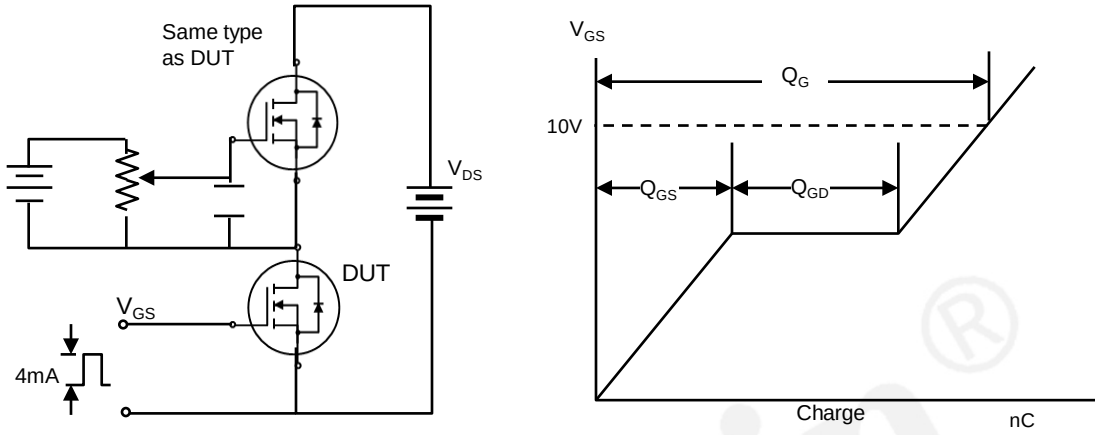


Fig. 13. Switching time test circuit & waveform

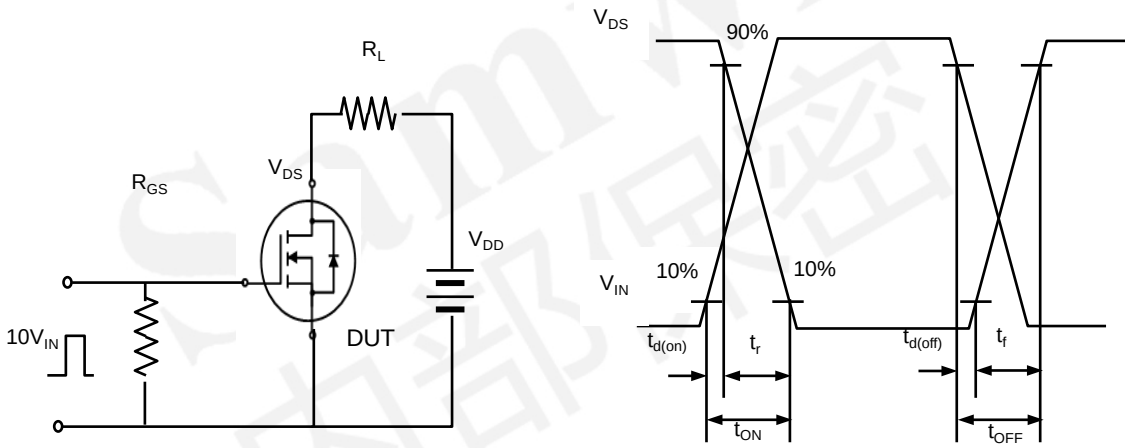


Fig. 14. Unclamped Inductive switching test circuit & waveform

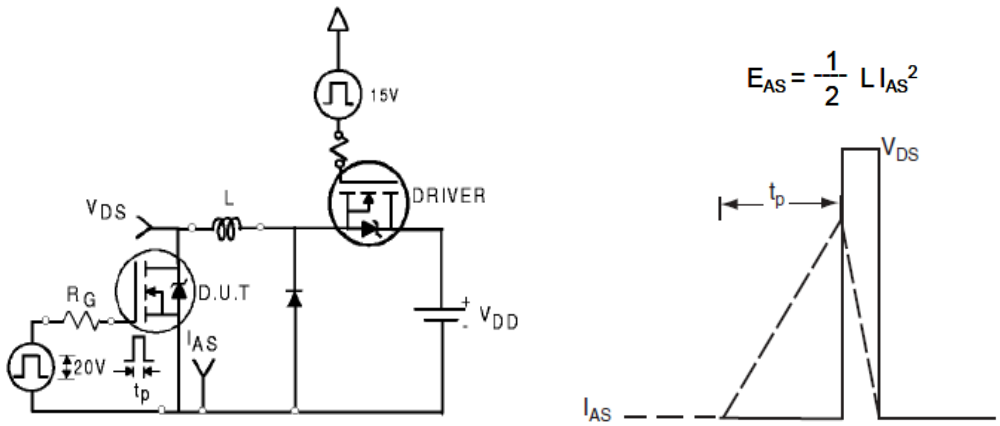
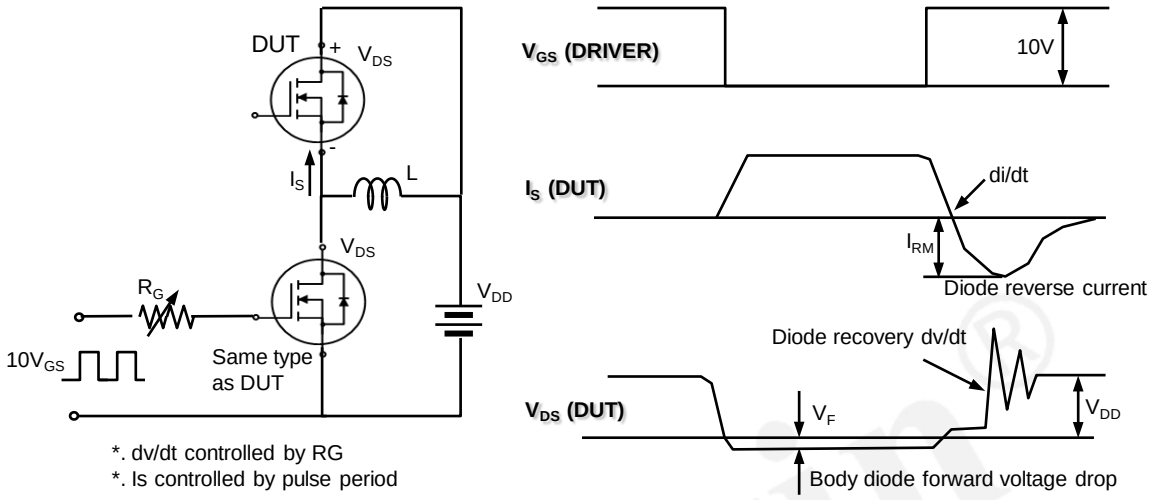


Fig. 15. Peak diode recovery dv/dt test circuit & waveform



DISCLAIRATION:

* All the data&curve within this document was tested in XI'AN SEMIPOWER TESTING&APPLICATION CENTER.
* This product has passed the PCT,TC,HTRB,HTGB,HAST,PC and Solderdunk reliability testing.
* Qualification Standards can also be found on the Web site (**http://www.semipower.com.cn**)
* Any advice, please send your proposal to **samwin@samwinsemi.com**